



TSM40N03PQ56

30V N-Channel Power MOSFET

PDFN56

8

Pin Definition:

1. Source	8. Drair
2. Source	7. Drair
3. Source	6. Drair
4. Gate	5. Drair

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
•	4.5 @ V _{GS} =10V	19
30	5.8 @ V _{GS} =4.5V	16

Features

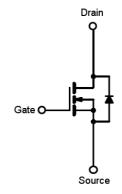
- Advanced Trench Technology
- Low On-Resistance
- Low gate charge typical @ 12nC (Typ.)
- Low Crss typical @ 140pF (Typ.)

Ordering Information

Part No.	Package	Packing
TSM40N03PQ56 RLG	PDFN56	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current	T _C =25℃		40		
	T _C =70℃		40	Α	
	T _A =25℃	l _D	31		
	T _A =70℃		25		
Drain Current-Pulsed Note 1		I _{DM}	100	Α	
Avalanche Current, L=0.5mH		I _{AS} , I _{AR}	38	Α	
Avalanche Energy, L=0.5mH		E _{AS} , E _{AR}	72	mJ	
	T _C =25℃		36		
Maximum Power Dissipation	T _C =70℃		23	W	
	T _A =25℃	P _D	4.2		
	T _A =70℃		2.7		
Storage Temperature Range		T _{STG}	-55 to +150	ပ္	
Operating Junction Temperature Range		TJ	-55 to +150	S	

^{*} Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R\Theta_{JC}$	3.5	°C/W
Thermal Resistance - Junction to Ambient	$R\Theta_{JA}$	30	°C/W

Notes: Surface mounted on FR4 board t ≤ 10sec

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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	30			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 19A$			3.5	4.5	mΩ
	$V_{GS} = 4.5V, I_D = 16A$	$R_{DS(ON)}$		4.6	5.8	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	1.15		2.2	V
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge	\\ 45\\ I 40\	Q_g		12		
Gate-Source Charge	$V_{DS} = 15V, I_{D} = 19A,$	Q_gs		5.4		nC
Gate-Drain Charge	$V_{GS} = 4.5V$	Q_{gd}		4.6		
Input Capacitance	- \/ 45\/ \/ 0\/	C_{iss}		1700		
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C _{oss}		350		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		140		
Switching						
Turn-On Delay Time		t _{d(on)}		25		
Turn-On Rise Time	$V_{GS} = 4.5V, V_{DS} = 15V,$	t _r		20		0
Turn-Off Delay Time	$R_G = 1\Omega$	$t_{d(off)}$		25		nS
Turn-Off Fall Time		t _f		15		
Drain-Source Diode Characteristic	s and Maximum Rating					
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =10A	V _{SD}		0.8	1.2	V
Reverse Recovery Time	I _S = 10A, T _J =25 °C	t _{fr}		25		nS
Reverse Recovery Charge	dl/dt = 100A/us	Q _{fr}		17		nC

Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. $R\theta_{JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R\theta_{JC}$ is guaranteed by design while $R\theta_{CA}$ is determined by the user's board design. $R\theta_{JA}$ shown below for single device operation on FR-4 in still air

3. The maximum current rating is limited by package.

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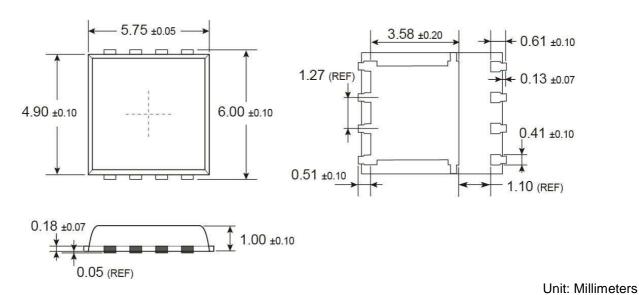


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PDFN56 Mechanical Drawing



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